Graphene a new electronic material

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Overview / Roadmap

- Introduction
- Preparation of Graphene
- Atomic / Electronic Structure
- Description as Dirac Fermions
- Anomalous Quantum Hall Effect
- Tunneling of Chiral Particles
- Graphene Devices
- Conclusions

Graphene: a carbon modification



AFM image of graphite surface, 2x2 nm² (Exp. Physics VI, Uni Augsburg)



Planar, hexagonal structure of graphene



Introduction

Graphene in many dimensions:

- 3D in graphite crystals
- 2D in a single layer
- 1D in nanotubes
- 0D in fullerenes



Preparation of Graphene

Top – Down Approach: Micromechanical cleavage

Bottom – Up Approach: Growing Graphene on SiC Top – Down Approach (after Novoselov et al., Science 306, 666 (2004))

"Micromechanical cleavage"

Recipe:

- 1. 1mm highly-oriented pyrolytic graphite (HOPG)
- 2. dry etching: 5µm
- 3. photoresist on glass surface, baking layer into it
- 4. peel of layers using scotch tape
- 5. release thin flake left on glass in acetone
- 6. "wash" flake on wafer
- 7. ultrasound cleaning in propanol: only thin flakes stick to SiO₂

Top – Down Approach

(after Novoselov et al., Science 306, 666 (2004))

Final step: selection process finding thin layers using optical microscope, scanning electron micrographs, AFM



Wafer with graphene flakes, optical microscope

Bottom-Up Approach

Growing Graphene on SiC



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Atomic Structure

sp² hybridization => planar, hexagonal lattice



- a = 2.45 Å
- 2 carbon atoms per unit cell

Electronic Bandstructure



- gapless semiconductor <=> semi-metal
- linear dispersion relation at conic point

Bipartite lattice





momentum space

real space

massless 2D Dirac Fermions



$$H_{K} = \begin{pmatrix} 0 & v_{F}(q_{x} - iq_{y}) \\ v_{F}(q_{x} + iq_{y}) & 0 \end{pmatrix}$$

• q = K - k

 2x2 structure from 2 site unit cell => pseudo spin

"light cone" with $v_{r} = 10^{6}$ m/s

Pseudo spin

$$H_{K} = \begin{pmatrix} 0 & v_{F}(q_{x} - iq_{y}) \\ v_{F}(q_{x} + iq_{y}) & 0 \end{pmatrix} = v_{F} \begin{pmatrix} \sigma_{x} & \sigma_{y} \end{pmatrix} \begin{pmatrix} q_{x} \\ q_{y} \end{pmatrix}$$

- Pseudo spin comutes with H_κ => is conserved
- Pseudo spin is projected on momentum
 σ parallel q <=> electron
 - σ antiparallel q <=> hole

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Anomalous QHE: setup

Landau quantisation

• from Schrödinger's Eq. (non relativistic):

$$E_n = \pm \hbar \, \omega_c \left(n + \frac{1}{2} \right)$$

electron/hole states



Landau quantisation (II)

• from Dirac Eq. (relativistic, massless):



Landau quantization (III)



- There is an zero energy level! It doesn't move!
- Landau levels
 degeneracy:
 - -E = 0 : 2x
 - E > 0 or < 0 : 4x

Understanding QHE: $\sigma_{_{XX}}$

Understanding QHE: σ_{xy}

Anomalous QHE in graphene



Hall bar, SEM false colors (L=200nm)

QHE in graphene

$$\sigma_{xy} = 4\left(\frac{e^2}{\hbar}\right)\left(n\pm\frac{1}{2}\right)$$

normal QHE

$$\sigma_{xy} = \left(\frac{e^2}{\hbar}\right)n$$



(Novoselov et al., Nature 2005)

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Tunneling of Chiral Particles

Motivation: 1D and 2D electron systems should crystalize at low temp. => the should be no conductivity

In graphene, this is not observed!!!



Forbidden Backscattering



Tunneling of Chiral Particles



electronic states outside the barrier meet holelike states inside the barrier

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Graphene Devices: Electron mobility

 Graphene: 20.000 cm²/Vs to 50.000 cm²/Vs (only limited by defects, stable btw. 10 to 100K)

Current technologies:

- Silicon: 10.000 cm²/Vs (max)
- InSb (indium antimonide): 30,000 cm²/Vs at 295K (Intel, Qinetq, 2005)

Classical FETs: n-MOSFET



n-MOSFET with channel



InSb quantum well transistors



(Intel, 3rd Asian Academic Forum, Nov. 2006)

Graphene FETs: simple design

direct application: Gas sensor

Conclusions & Outlook

- unexpected bridge btw. condensed matter & QFT
- possibility to study 2D massless Dirac fermions in a bench-top setup
- (anomalous QHE, absence of Anderson localisation)
- Carbon transistors, with ballistic transport
- even more possibilities with bilayer graphene!

any questions?

THE END

Thank you for your attention. Have a nice day.